TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LCX16373AFT

Low-Voltage 16-Bit D-Type Latch with 5-V Tolerant Inputs and Outputs

The TC74LCX16373AFT is a high-performance CMOS 16-bit D-type latch. Designed for use in 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

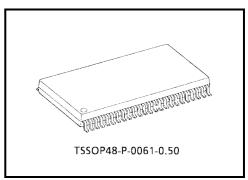
The device is designed for low-voltage $(3.3 \text{ V}) \text{ V}_{CC}$ applications, but it could be used to interface to 5-V supply environment for both inputs and outputs.

This 16-bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the \overline{OE} input is high, the outputs are in a high-impedance state.

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: V_{CC} = 2.0 to 3.6 V
- High-speed operation: $t_{pd} = 7.0 \text{ ns} (max) (V_{CC} = 3.0 \text{ to } 3.6 \text{ V})$
- Ouput current: $|I_{OH}|/I_{OL} = 24 \text{ mA} (\text{min}) (V_{CC} = 3.0 \text{ V})$
- Latch-up performance: ±500 mA
- Package: TSSOP (thin shrink small outline package)
- Power-down protection provided on all inputs and outputs



Weight: 0.25 g (typ.)

Pin Assignment (top view)

			1	
10E	1	\bigcirc	48	1LE
1Q1	2		47	1D1
1Q2	3		46	1D2
GND	4		45	GND
1Q3	5		44	1D3
1Q4	6		43	1D4
V _{CC}	7		42	V _{CC}
1Q5	8		41	1D5
1Q6	9		40	1D6
GND	10		39	GND
1Q7	11		38	1D7
1Q8	12		37	1D8
2Q1	13		36	2D1
2Q2	14		35	2D2
GND	15		34	GND
2Q3	16		33	2D3
2Q4	17		32	2D4
V _{CC}	18		31	V _{CC}
2Q5	19		30	2D5
2Q6	20		29	2D6
GND	21		28	GND
2Q7	22		27	2D7
2Q8	23		26	2D8
$2\overline{OE}$	24		25	2LE
			1	

IEC Logic Symbol

10E -	1	1EN		
1LE -	48	СЗ		
2 <mark>0E</mark> -	24	2EN		
2LE -	25	C4		
1D1 -	47	3D 1 ▽	2	1Q1
1D2 -	46	· · · · · · · · · · · · · · · · · · ·	3	1Q2
1D3 -	44	 	5	1Q3
1D4 -	43		6	1Q4
1D5 -	41		8	1Q5
1D6 -	40		9	1Q6
1D7 -	38		11	1Q7
1D8 -	37		12	1Q8
2D1 -	36	4D 2 🗸	13	2Q1
2D1 -	35		14	2Q2
2D2 -	33		16	2Q2 2Q3
2D3 2D4 -	32		17	2Q3 2Q4
2D4 2D5 -	30		19	2Q4 2Q5
2D5 2D6 -	29		20	
	27		22	2Q6
2D7 -	26]	23	2Q7
2D8 -		L	J	2Q8

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Truth Table

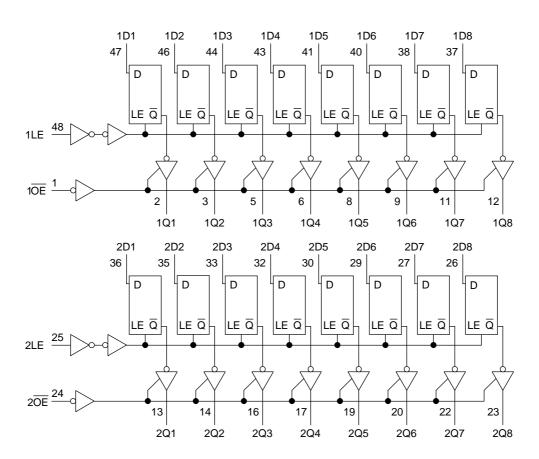
	Inputs					
1 0E	1LE	1D1-1D8	1Q1-1Q8			
Н	Х	Х	Z			
L	L	Х	Qn			
L	Н	L	L			
L	Н	Н	Н			

	Inputs		Outputs
2 0E	2LE	2D1-2D8	2Q1-2Q8
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 7.0	V
Input voltage	V _{IN}	-0.5 to 7.0	V
		-0.5 to 7.0 (Note 1)	
Output voltage	VOUT	-0.5 to V _{CC} + 0.5	V
		(Note 2)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 3)	mA
DC output current	IOUT	±50	mA
Power dissipation	PD	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Output in OFF state

Note 2: High or low state. $I_{\mbox{OUT}}$ absolute maximum rating must be observed.

Note 3: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Conditions

Characteristics Sym		Rating	Unit		
Power supply voltage	V _{CC}	2.0 to 3.6	V		
i ower supply voltage	VCC	1.5 to 3.6 (Note 4)	v		
Input voltage	V _{IN}	0 to 5.5	V		
Output voltage	Vout	0 to 5.5 (Note 5)	V		
Output voltage	VOUT	0 to V _{CC} (Note 6)	v		
Output current	1/1	±24 (Note 7)	mA		
	I _{OH} /I _{OL}	±12 (Note 8)	ША		
Operating temperature	T _{opr}	-40 to 85	°C		
Input rise and fall time	dt/dv	0 to 10 (Note 9)	ns/V		

Note 4: Data retention only

Note 5: Output in OFF state

Note 6: High or low state

Note 7: $V_{CC} = 3.0$ to 3.6 V

Note 8: $V_{CC} = 2.7$ to 3.0 V

Note 9: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics (Ta = -40 to 85° C)

Characte	ristics	Symbol	Test (Condition	V _{CC} (V)	Min	Max	Unit
lanut velte en	H-level	VIH			2.7 to 3.6	2.0		V
Input voltage	L-level	VIL			2.7 to 3.6		0.8	V
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	VOH	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -12 mA	2.7	2.2		
		-		I _{OH} = -18 mA	3.0	2.4	_	
Output voltage				I _{OH} = -24 mA	3.0	2.2	_	V
				I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
	L-level			I _{OL} = 12 mA	2.7	_	0.4	
	L-level	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 16 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	nt	I _{IN}	$V_{IN} = 0$ to 5.5 V		2.7 to 3.6		±5.0	μA
3-state output OFF	state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		2.7 to 3.6		±5.0	μA
Power-off leakage	current	IOFF	$V_{IN}/V_{OUT} = 5.5 V$		0		10.0	μA
	urroot		$V_{IN} = V_{CC}$ or GND		2.7 to 3.6		20.0	
Quiescent supply current		ICC	$V_{IN}/V_{OUT} = 3.6 \text{ to } 5.5 \text{ V}$		2.7 to 3.6		±20.0	μA
Increase in Icc per	input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6		500	

AC Characteristics (Ta = -40 to 85°C)

Characteristics	Symbol	Test Condition		Min	Max	Unit
	-,	-,				
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.7		8.0	ns
(D-Q)	t _{pHL}		$\textbf{3.3}\pm\textbf{0.3}$	1.5	7.0	115
Propagation delay time	t _{pLH}		2.7		8.0	
(LE-Q)	t _{pHL}	Figure 1, Figure 2	$\textbf{3.3}\pm\textbf{0.3}$	1.5	7.0	ns
O state sutaut enchie time	t _{pZL}	Figure 4 Figure 2	2.7	_	8.2	
3-state output enable time	t _{pZH}	Figure 1, Figure 3	$\textbf{3.3}\pm\textbf{0.3}$	1.5	7.2	ns
O state sutrut disable time	t _{pLZ}	Figure 4. Figure 2	2.7		8.2	
3-state output disable time	t _{pHZ}	Figure 1, Figure 3	$\textbf{3.3}\pm\textbf{0.3}$	1.5	7.2	ns
Minimum pulse width	t (11)	Figure 4 Figure 2	2.7	4.0		
(LE)	t _w (H)	Figure 1, Figure 2	$\textbf{3.3}\pm\textbf{0.3}$	3.0	_	ns
		Figure 4. Figure 2	2.7	2.5	_	
Minimum setup time t _s	ι _s	Figure 1, Figure 2	$\textbf{3.3}\pm\textbf{0.3}$	2.5		ns
Minimum hold time		Figure 1. Figure 2	2.7	1.5		
Minimum hold time	t _h	Figure 1, Figure 2	$\textbf{3.3}\pm\textbf{0.3}$	1.5	_	ns
	t _{osLH}	2.7	_	—		
Output to output skew	t _{osHL}	(Note 10)	$\textbf{3.3}\pm\textbf{0.3}$		1.0	ns

Note 10: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.5 \text{ ns}$, $C_L = 50 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	3.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	—		3.3	7	pF
Output capacitance	C _{OUT}			3.3	8	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (Note 11)	3.3	25	pF

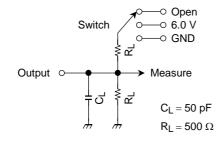
Note 11: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 (per bit)$

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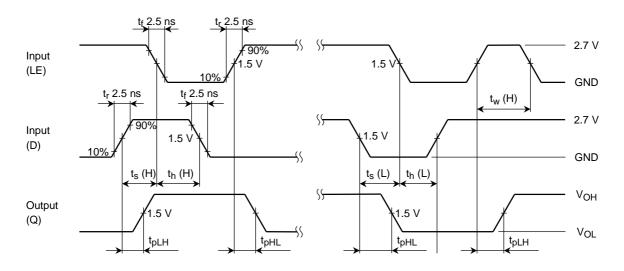
AC Test Circuit



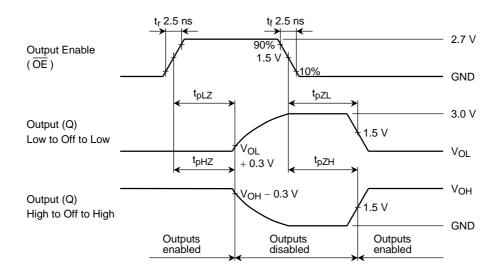
Parameter	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	6.0 V
t _{pHZ} , t _{pZH}	GND
t _w , t _s , t _h ,	Open

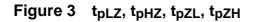


AC Waveform



 $\label{eq:Figure 2} \quad t_{pLH}, \, t_{pHL}, \, t_w, \, t_s, \, t_h$

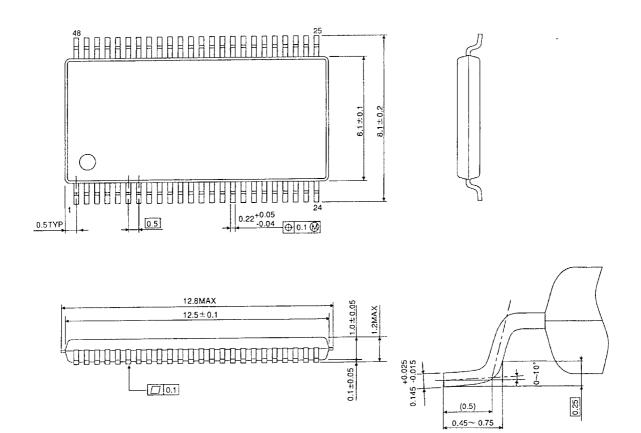




Package Dimensions

TSSOP48-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

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